Form PTO-1449 (modified)	Atty. Docket No. 2000.093282/TT5101D	Serial No. Unknown
List of Patents and Publications for Applicant's INFORMATION DISCLOSURE STATEMENT	Applicant Andy C. Wei, Derick J. Wristers and Mark S. Fuselier	
(Use several sheets if necessary)	Filing Date: March 9, 2004	Group: Unknown

U.S. Patent Documents	Foreign Patent Documents	Other Art
See Page 1	*See Page 1*	*See Page 1*

U.S. Patent Documents

Exam. Init.	Ref. Des.	Document Number	Date	Name	Class	Sub Class	Filing Date of App.
SDT	A1	5,482871	01-1996	Pollack	438	151	
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Foreign Patent Documents

Exam. Init.	Ref. Des.	Document Number	Date	Country	Class	Sub Class	Translation Yes/No
	B1						
	B2						
	B3						

Other Art (Including Author, Title, Date Pertinent Pages, Etc.)

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SDT	C1	Baine *et al.*, "Back Gate Effects in N-Channel Monocrystalline Silicon Devices-on-Glass and Their Suppression by Boron Ion Implantation," *Mat. Res. Soc. Symp. Proc.*, 558:369-74, 2000
	C2	Chang *et al.*, "Efficacy of Air in Reducing the Kink Effect on Floating-Body NFD/SOI CMOS," *Proc. 1998 IEEE Int'l SOI Conf.*, pp. 155-56, 1998
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EXAMINER: Stanetta Isaac | DATE CONSIDERED: 07/13/04

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